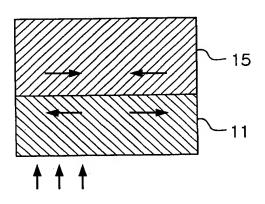
## METHOD FOR MANUFACTURING GALLIUM NITRIDE(GaN) BASED SINGLE

CRYSTALLINE SUBSTRATE
Inventor: NA, Jeong Seok et al.
Docket No. 2336-195

1/3



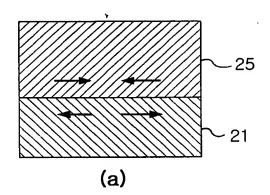
**PRIOR ART** 

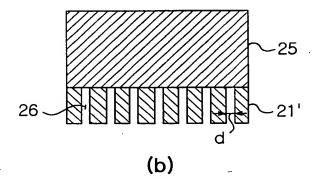
FIG. 1

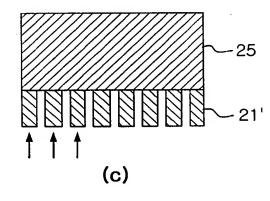
## METHOD FOR MANUFACTURING GALLIUM NITRIDE(GaN) BASED SINGLE

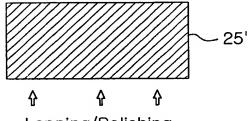
CRYSTALLINE SUBSTRATE

Inventor: NA, Jeong Seok et al.
Docket No. 2336-195
2/3







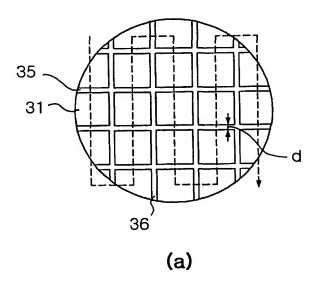


Lapping/Polishing

(d)

FIG. 2

## METHOD FOR MANUFACTURING GALLIUM NITRIDE(GaN) BASED SINGLE CRYSTALLINE SUBSTRATE Inventor: NA, Jeong Seok et al. Docket No. 2336-195 3/3



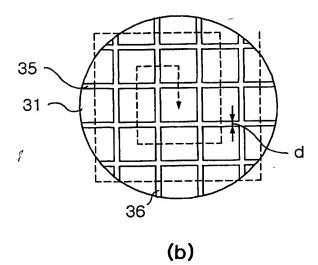


FIG. 3